

## TP1220L, TP/VP2020L, BSS92

Siliconix

### P-Channel Enhancement-Mode MOS Transistors

#### Product Summary

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max ( $\Omega$ )	$V_{GS(th)}$ (V)	$I_D$ (A)
TP1220L	-120	20 @ $V_{GS} = -4.5$ V	-1 to -2.4	-0.12
TP2020L	-200	20 @ $V_{GS} = -4.5$ V	-1 to -2.4	-0.12
VP2020L	-200	20 @ $V_{GS} = -4.5$ V	-0.8 to -2.5	-0.12
BSS92	-200	20 @ $V_{GS} = -10$ V	-0.8 to -2.8	-0.15

#### Features

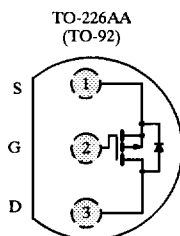
- High-Side Switching
- Secondary Breakdown Free: -220 V
- Low On-Resistance: 11.5  $\Omega$
- Low-Power/Voltage Driven
- Excellent Thermal Stability

#### Benefits

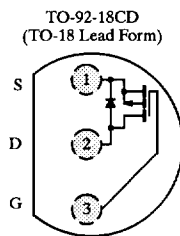
- Ease in Driving Switches
- Full-Voltage Operation
- Low Offset Voltage
- Easily Driven Without Buffer
- No High-Temperature "Run-Away"

#### Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Power Supply, Converters
- Motor Control
- Switches



Top View  
TP1220L  
TP2020L  
VP2020L



Top View  
BSS92

#### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	TP1220L	TP2020L	VP2020L	BSS92	Unit
Drain-Source Voltage	$V_{DS}$	-120	-200	-200	-200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	$\pm 20$	$\pm 20$	V
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ )	$I_D$	$T_A = 25^\circ\text{C}$	-0.12	-0.12	-0.12	-0.15
		$T_A = 100^\circ\text{C}$	-0.08	-0.08	-0.08	-0.09
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	-0.48	-0.48	-0.48	-0.6	A
Power Dissipation	$P_D$	$T_A = 25^\circ\text{C}$	0.8	0.8	0.8	1.0
		$T_A = 100^\circ\text{C}$	0.32	0.32	0.32	0.4
Maximum Junction-to-Ambient	$R_{thJA}$	156	156	156	125	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150				$^\circ\text{C}$

#### Notes

a. Pulse width limited by maximum junction temperature.

### Specifications<sup>a</sup>

Parameter	Symbol	Test Conditions	Typ <sup>b</sup>	Limits						Unit	
				TP1220L TP2020L		VP2020L		BSS92			
				Min	Max	Min	Max	Min	Max		
<b>Static</b>											
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ $I_D = -10\text{ }\mu\text{A}$	TP1220L	-200	-120						V
			TP2020L	-220	-200						
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-220						-200		
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1\text{ mA}$	-1.9	-1	-2.4	-0.8	-2.5	-0.8	-2.8		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ $T_J = 125^\circ\text{C}$			$\pm 10$		$\pm 10$		$\pm 100$	nA	
					$\pm 50$		$\pm 50$				
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 0.8 \times V_{(BR)DSS}, V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			-1		-1			$\mu\text{A}$	
					-100		-100				
		$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$							-60		
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$							-200		
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$							-0.2		
On-State Drain Current <sup>c</sup>	$I_{D(on)}$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}$	-250	-50		-100				mA	
Drain-Source On-Resistance <sup>c</sup>	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -0.1\text{ A}$	11.5		20				20	$\Omega$	
		$V_{GS} = -4.5\text{ V}, I_D = -0.1\text{ A}$	15				20				
		$T_J = 125^\circ\text{C}$	28				40				
		$V_{GS} = -4.5\text{ V}, I_D = -0.05\text{ A}$	15		20						
		$T_J = 125^\circ\text{C}$	28		40						
Forward Transconductance <sup>c</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -0.1\text{ A}$	170	60		100				mS	
		$V_{DS} = -25\text{ V}, I_D = -0.1\text{ A}$	170					60			
Diode Forward Voltage	$V_{SD}$	$I_S = -0.3\text{ A}, V_{GS} = 0\text{ V}$	-0.9						-1.2	V	
<b>Dynamic</b>											
Input Capacitance	$C_{iss}$	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$	30		60		70			pF	
Output Capacitance	$C_{oss}$		10		20		20				
Reverse Transfer Capacitance	$C_{rss}$		3		10		10				
<b>Switching<sup>d</sup></b>											
Turn-On Time	$t_{ON}$	$V_{DD} = -25\text{ V}, R_L = 250\text{ }\Omega$ $I_D \approx -0.1\text{ A}, V_{GEN} = -10\text{ V}$ $R_G = 25\text{ }\Omega$	14		25					ns	
	$t_{d(on)}$		6				10				
	$t_r$		8				15				
Turn-Off Time	$t_{OFF}$		35		55						
	$t_{d(off)}$		18				30				
	$t_f$		17				25				

Notes

- a.  $T_A = 25^\circ\text{C}$  unless otherwise noted.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Pulse test:  $PW \leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .
- d. Switching time is essentially independent of operating temperature.

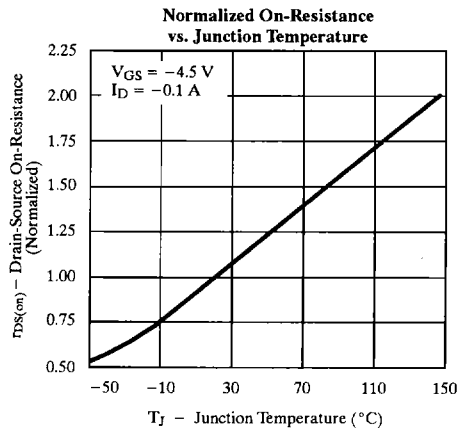
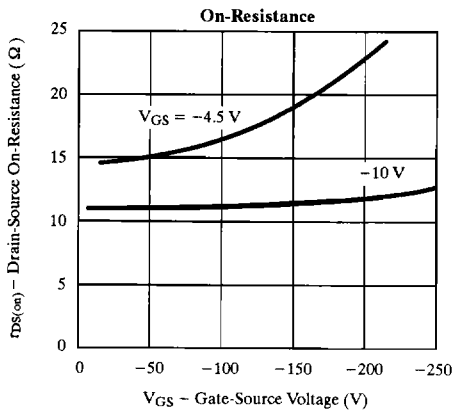
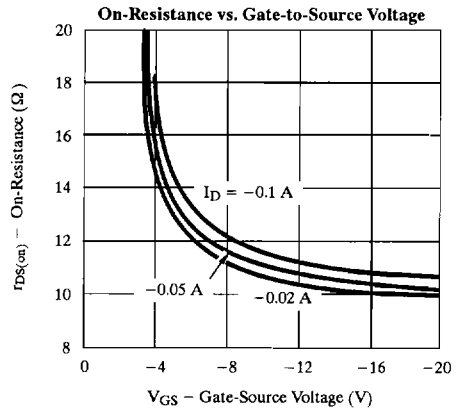
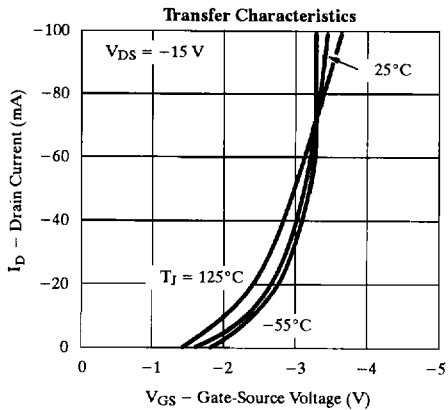
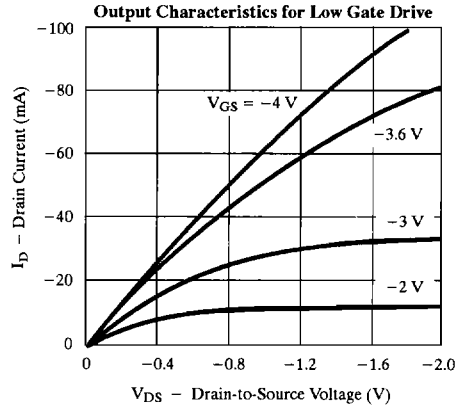
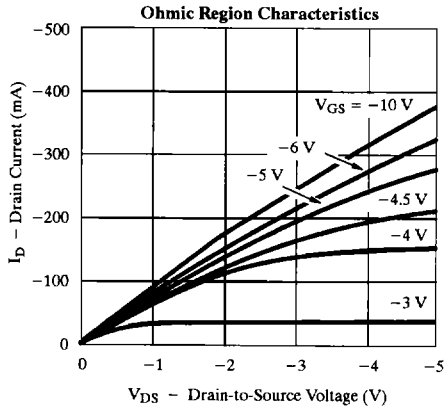
VPDQ20



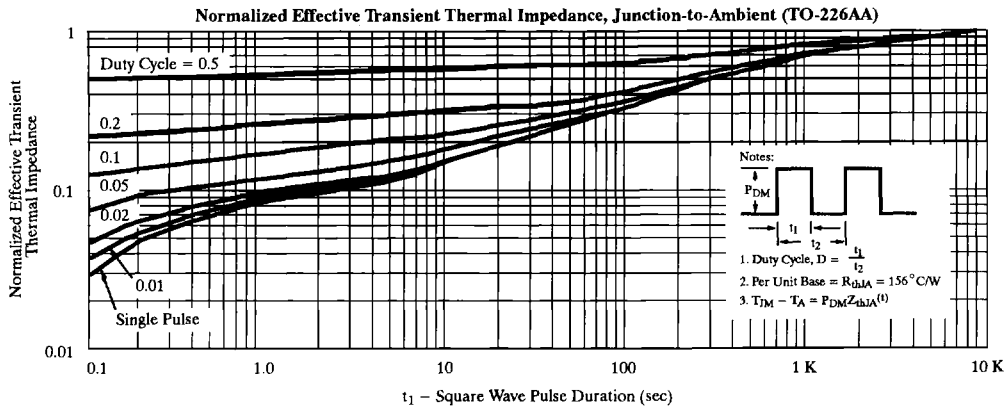
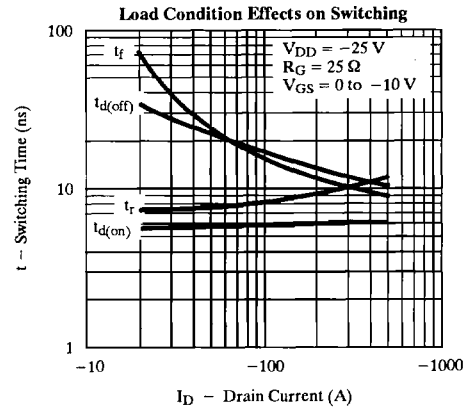
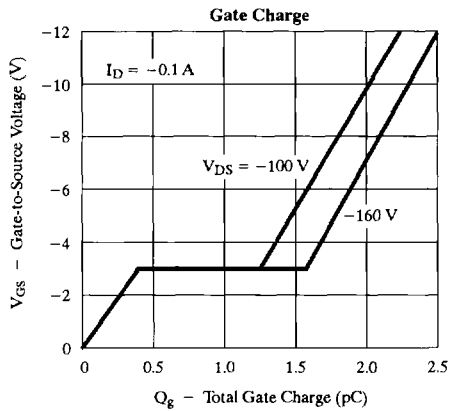
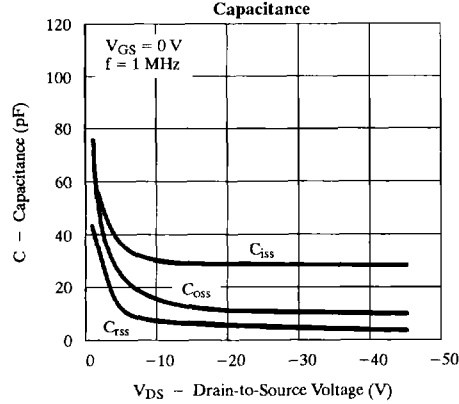
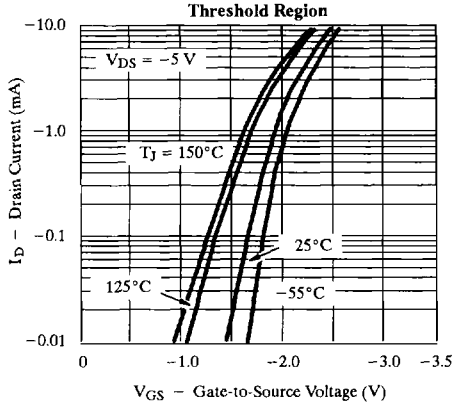
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### Typical Characteristics (25°C Unless Otherwise Noted)



### Typical Characteristics (25°C Unless Otherwise Noted) (Cont'd)



Low Power MOS